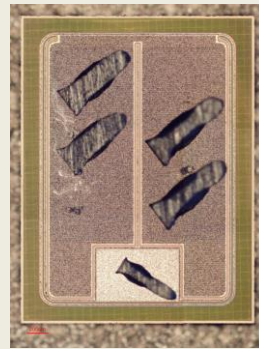


## **ANALYSIS REPORT THE WOLFSPEED C3M0065090D 3<sup>rd</sup> GENERATION SiC POWER MOSFET**

**June, 2016.** LTEC Corporation released the structure and process analysis report of WOLFSPEED (CREE) 3<sup>rd</sup> generation SiC Power MOSFET device having 20% lower on-resistance than its 2nd generation predecessor.



**Package**



**Die**

This 114 page report has two parts: a detailed structure analysis section including process-flow section reconstructed based upon associated Cree patents, listed in the 2<sup>nd</sup> half of the report.

### **Device features**

- **Maximum operating voltage : 900V, rated DC Drain current ID @25°C : 36A**
- **Very low specific On-resistance, RON x A= 423mΩ x mm<sup>2</sup>**  
**reference data : Si SJMOS C7 RON x A = ~1000mΩ x mm<sup>2</sup>.**

This report reveals the device structure, materials and technology that resulted in such a significant reduction of its on-resistance.

- Transistor structure analysis
- Self-aligned process for formation of the channel region
- N epitaxial layer, analysis of the doping concentration profile
- List of relevant references and patents of CREE's SiC MOSFET

Note: The listed report price may not be accurate as it decreases over time.

Please contact us for current report pricing : [info@ltecusa.com](mailto:info@ltecusa.com)

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